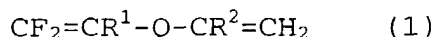


ABSTRACT OF THE DISCLOSURE

To provide a chemical amplification type resist composition which is excellent in transparency to a radiation and in dry etching properties and which gives a resist pattern excellent in sensitivity, resolution, evenness, heat resistance, etc. A resist composition comprising a fluoropolymer (A) which is a fluoropolymer having repeating units formed by cyclopolymerization of a fluorinated diene represented by the formula (1) and which has blocked acidic groups as Q, an acid-generating compound (B) which generates an acid under irradiation with light, and an organic solvent (C):



wherein each of  $\text{R}^1$  and  $\text{R}^2$  which are independent of each other, is a hydrogen atom, a fluorine atom, a methyl group or a trifluoromethyl group, and Q is a bivalent organic group having a blocked acidic group capable of forming an acidic group by an acid or a group which can be converted to such a blocked acidic group.